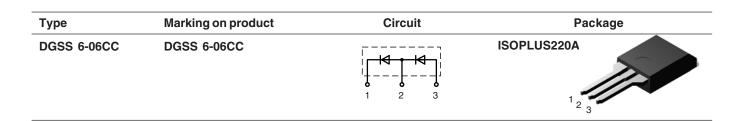


Gallium Arsenide Schottky Rectifier

Second generation ISOPLUS220[™] **Electrically Isolated Back Surface**

Preliminary Data

V_{RRM} = 600 V (2x300V) I_{DC} = 11 A $C_{Junction} = 4 \text{ pF}$



Diode					
Symbol	Conditions	Maximum Ratings			
V _{RRM/RSM} V _{RRM/RSM}	(between terminal 1 and 3)	600 300	V V		
I _{FAV} I _{FAV}	$T_c = 25^{\circ}C; DC$ $T_c = 90^{\circ}C; DC$	11 6	A A		
I _{FSM}	$T_{v_J} = 45^{\circ}C; t_p = 10 \text{ ms} (50 \text{ Hz}), \text{ sine}$	30	А		
P _{tot}	$T_c = 25^{\circ}C$	12	W		

Symbol	Conditions Characte min. typ			istic Values . max.	
V _F	$I_F = 6 A;$ $T_{VJ} = 25^{\circ}C$ $I_F = 6 A;$ $T_{VJ} = 125^{\circ}C$		1.7 1.2	2.1 V V	
I _R	$ \begin{array}{l} V_{\text{R}} = V_{\text{RRM}}; \ \ T_{\text{VJ}} = \ 25^{\circ}\text{C} \\ V_{\text{R}} = V_{\text{RRM}}; \ \ T_{\text{VJ}} = \ 125^{\circ}\text{C} \end{array} $		15	0.15 mA μA	
l _{RM} t _{rr}	$\label{eq:linear} \left. \begin{array}{l} I_{\rm F} = 2 \; {\rm A}; & - di_{\rm F}/dt = 150 \; {\rm A}/\mu {\rm s}; \\ V_{\rm R} = 150 \; {\rm V}; & T_{\rm VJ} = 125^{\circ}{\rm C} \end{array} \right.$		0.6 20	A ns	
C	$V_{R} = 150 \text{ V}; T_{VJ} = 125^{\circ}\text{C}$		4	pF	
R _{thJC}				12.5 K/W	

Data according to IEC 60747 and per diode unless otherwise specified

Features

GaAs Schottky Diode with Enhanced Barrier Height:

- · lowest operating forward voltage drop due to additional injection of minority carriers
- high switching speed
- low junction capacity of GaAs diode independent from temperature
- short and low reverse recovery current peak due to short lifetime of minority carriers
- soft turn off
- low leakage current
- ISOPLUS220[™] Package:
- · isolated back surface
- · low coupling capacy between pins and heatsink
- enlarged creepage
- high reliability
- industry standard outline

Applications

Power Factor Correction (PFC) Switched Mode Power Supplies:

• AC-DC converters • DC-DC converters

with:

- high switching frequency
- high efficiency
- low EMI

for use e.g. in:

- telecom
- computer
- automotive equipment

LIXYS

Component					
Symbol	Conditions	Maximum Ratings			
I _{RMS}	per pin	45	А		
T _{VJ} T _{stg}		-55+175 -55+150	°C ℃		
VISOL	$I_{ISOL} \le 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~		
F _c	mounting force with clip	1050	Ν		

Symbol	Conditions	Chara min.	acteris typ.	tic Values max.
C _p	coupling capacity between shorted pins and mounting tab in the case		15	pF
R _{thCS}			0.3	K/W
Weight			2	g

